Switching (200V, 5A)

RDN050N20

●Features

1) Low on-resistance.
2) Low input capacitance.
3) Exellent resistance to damage from static electricity.

●Application

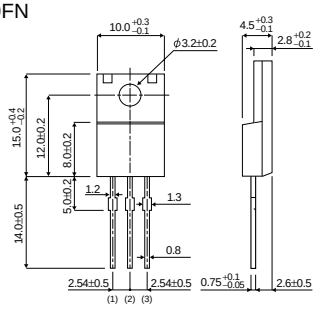
Switching

●Structure

Silicon N-channel
MOS FET

●External dimensions (Units : mm)

TO-220FN



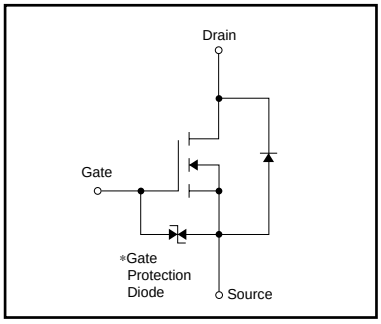
(1) Gate
(2) Drain
(3) Source

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V_{DSS}	200	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	5	A
	Pulsed	I_{DP} *1	20	A
Reverse Drain Current	Continuous	I_{DR}	5	A
	Pulsed	I_{DRP} *1	20	A
Avalanche Current		I_{AS} *2	5	A
Avalanche Energy		E_{AS} *2	75	mJ
Total Power Dissipation (T_C=25°C)		P_D	30	W
Channel Temperature		T_{ch}	150	°C
Storage Temperature		T_{stg}	−55 to 150	°C

*1 Pw ≤ 10µs, Duty cycle ≤ 1%
*2 L≒ 4.5mH, V_{DD}=50V, R_G=25Ω, 1Pulse, Tch=25°C

●Equivalent Circuit



*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-Source Leakage	I_{GSS}	—	—	±10	μA	V_{GS}=±30V, V_{GS}=0V
Drain-Source Breakdown Voltage	$V_{(BR)\ DSS}$	200	—	—	V	I_D=250μA, V_{GS}=0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	25	μA	V_{DS}=200V, V_{GS}=0V
Gate Threshold Voltage	$V_{GS\ (th)}$	2.0	—	4.0	V	V_{DS}=10V, I_D=1mA
Static Drain-Source On-State Resistance	$R_{DS\ (on)}$	—	0.55	0.72	Ω	I_D=2.5A, V_{GS}=10V
Forward Transfer Admittance	$\|Y_{fs}\|$	1.1	1.8	—	S	V_{DS}=10V, I_D=2.5A
Input Capacitance	C_{iss}	—	292	—	pF	V_{DS}=10V
Output Capacitance	C_{oss}	—	92	—	pF	V_{GS}=0V
Reverse Transfer Capacitance	C_{rss}	—	28	—	pF	f=1MHz
Turn-On Delay Time	$t_{d\ (on)}$	—	10	—	ns	I_D=2.5A, V_{DD} ≒100V
Rise Time	t_r	—	22	—	ns	V_{GS}=10V
Turn-Off Delay Time	$t_{d\ (off)}$	—	23	—	ns	R_L=40Ω
Fall Time	t_f	—	28	—	ns	R_{GS}=10Ω
Reverse Recovery Time	t_{rr}	—	117	—	ns	I_{DR}=5A, V_{GS}=0V
Reverse Recovery Charge	Q_{rr}	—	0.37	—	μC	di / dt=100A / μs
Total Gate Charge	Q_g	—	9.3	—	nC	V_{DD}=100V, V_{GS}=10V, I_D=5A

●**Electrical characteristic curves**

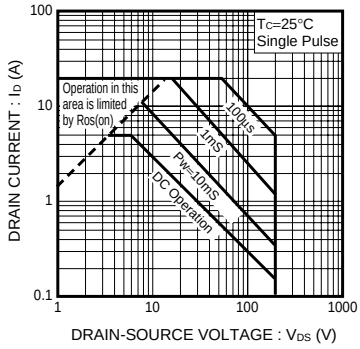


Fig.1 Maximun Safe Operating Area

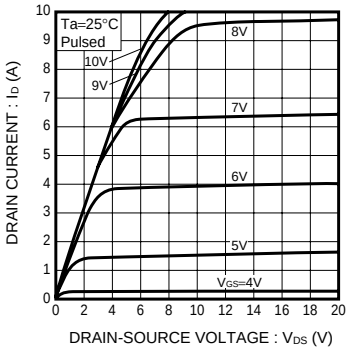


Fig.2 Typical Output Characteristics

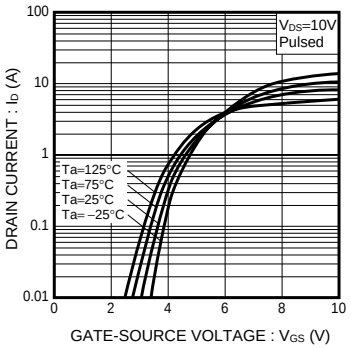


Fig.3 Typical Transfer Characteristics

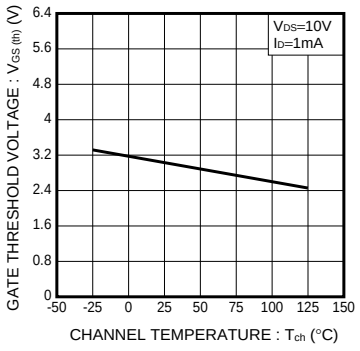


Fig.4 Gate Threshold Voltage vs. Channel Temperature

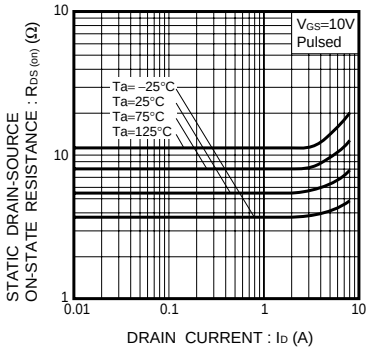


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

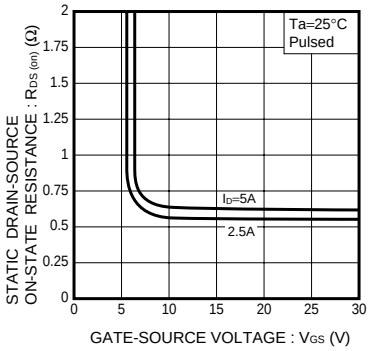


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

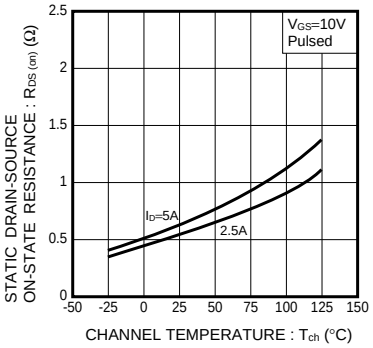


Fig.7 Static Drain-Source On-State Resistance vs. Channel Temperature

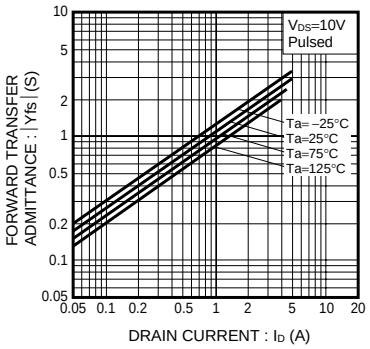


Fig.8 Forward Transfer Admittance vs. Drain Current

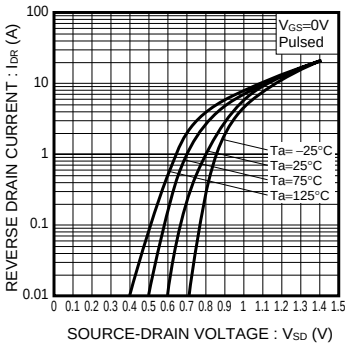


Fig.9 Reverse Drain Current vs. Source-Drain Voltage

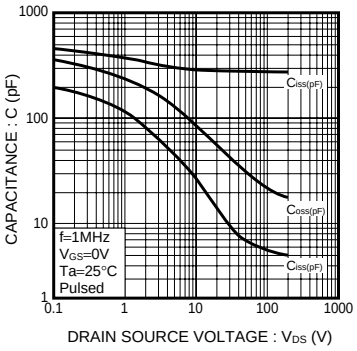


Fig.10 Typical Capacitance vs. Drain-Source Voltage

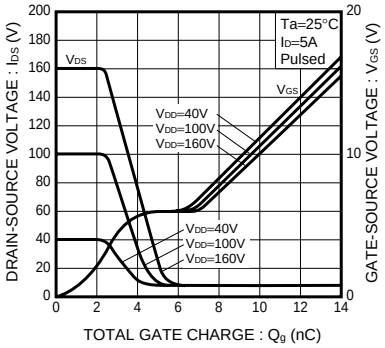


Fig.11 Dynamic Input Characteristics

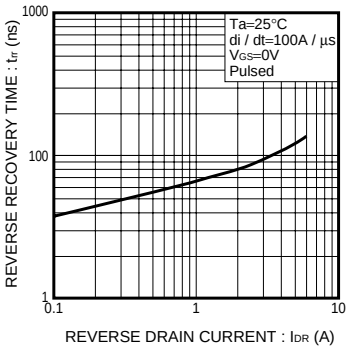


Fig.12 Reverse Recovery Time vs. Reverse Drain Current

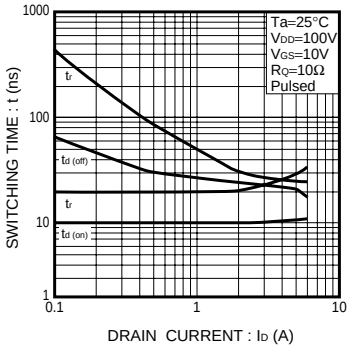


Fig.13 Switching Characteristcs

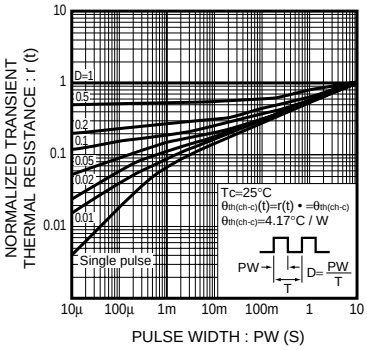


Fig.14 Normalized Transient Thermal Resistance vs. Pulse Width

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